UNIKC Semiconductor

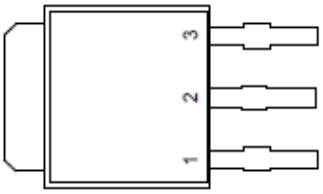
RoHS Compliant

P0260EIS

N-Channel Enhancement Mode MOSFET

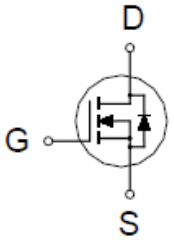
PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
600V	4.4Ω @V_{GS} = 10V	2A



1.GATE
2.DRAIN
3.SOURCE

TO-251(IS)



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	
Continuous Drain Current[2]	T_C = 25 °C	I_D	2	A
	T_C = 100 °C		1.4	
Pulsed Drain Current[1,2]		I_{DM}	8	
Avalanche Current[3]		I_{AS}	2	
Avalanche Energy[3]		E_{AS}	20	mJ
Power Dissipation	T_C = 25 °C	P_D	56	W
	T_C = 100 °C		22	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.2	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Limited only by maximum temperature allowed

[3]V_{DD} = 50V , L = 10mH ,starting T_J = 25 ° C

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	600			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3.1	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±100	nA
Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V, T_C = 25 °C			1	μA
		V_{DS} = 480V, V_{GS} = 0V , T_C = 100 °			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 1A		3.5	4.4	Ω
Forward Transconductance[1]	g_{fs}	V_{DS} = 15V, I_D = 2A		4		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		322		pF
Output Capacitance	C_{oss}			39		
Reverse Transfer Capacitance	C_{rss}			7		
Total Gate Charge[2]	Q_g	V_{DD} = 480V, I_D = 2A,V_{GS}= 10V		10.4		nC
Gate-Source Charge[2]	Q_{gs}			1.7		
Gate-Drain Charge[2]	Q_{gd}			4.4		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 300V, I_D = 2A, V_{GS} = 10V, R_G = 25Ω		28		nS
Rise Time[2]	t_r			60		
Turn-Off Delay Time[2]	$t_{d(off)}$			58		
Fall Time[2]	t_f			66		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				2	A
Forward Voltage[1]	V_{SD}	I_F = 2A, V_{GS} = 0V			1.5	V
Reverse Recovery Time	t_{rr}	I_F = 2A, dI_F/dt = 100A / μS		285		nS
Reverse Recovery Charge	Q_{rr}			1.2		uC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

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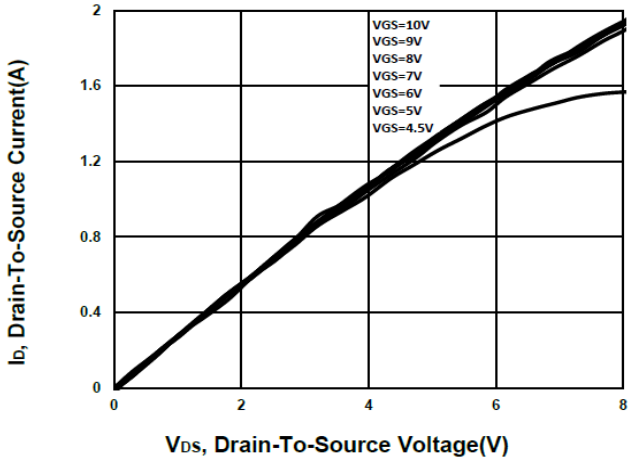
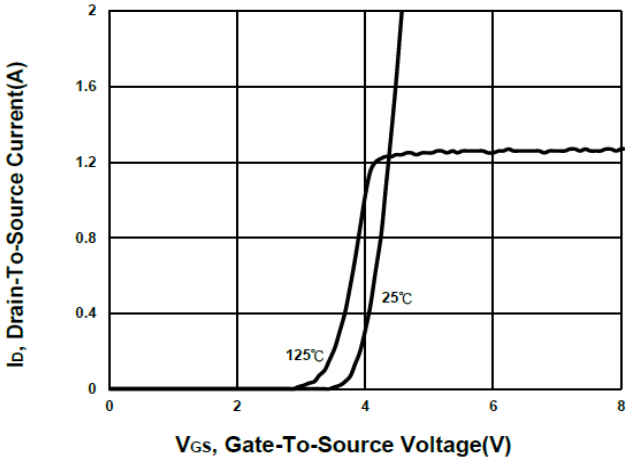
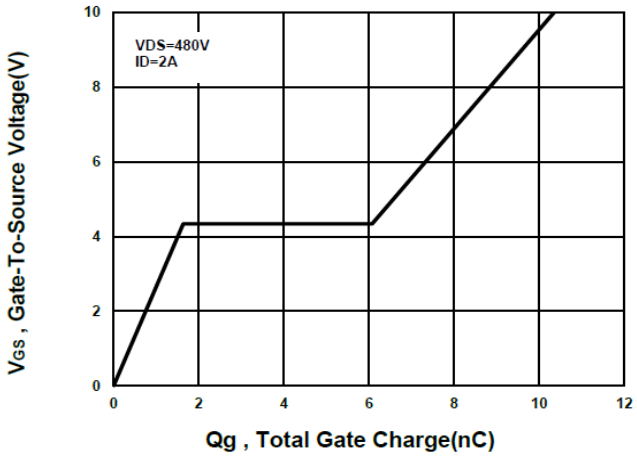
Output Characteristics



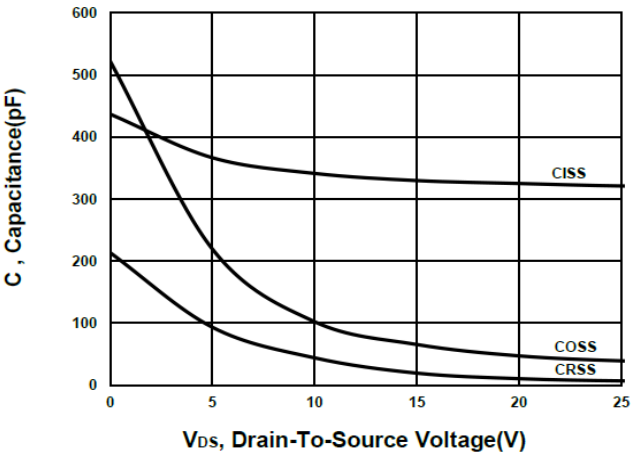
Transfer Characteristics



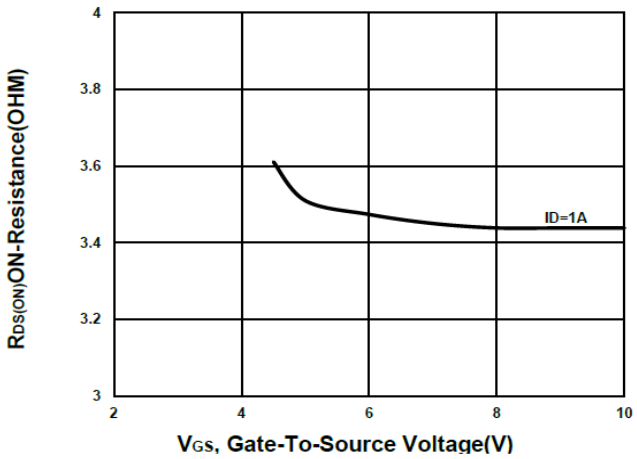
Gate charge Characteristics



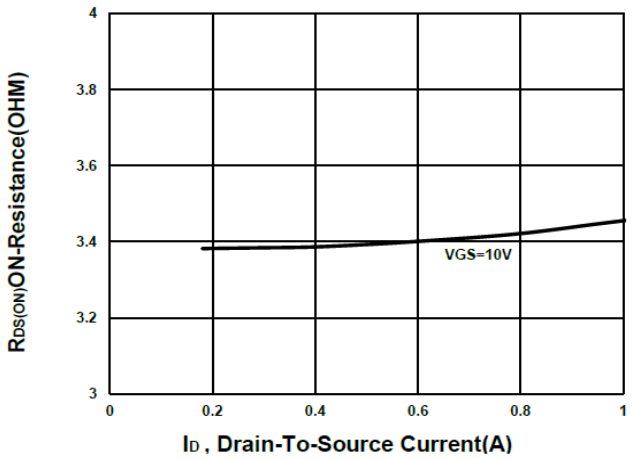
Capacitance Characteristic



On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



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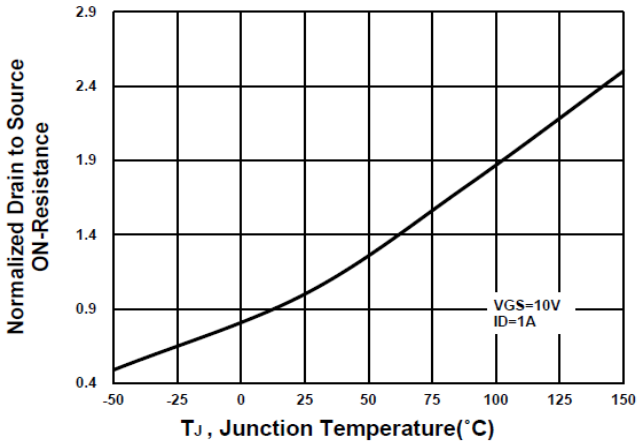
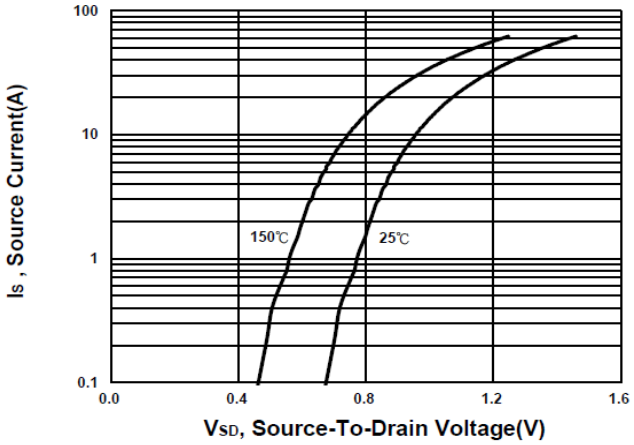
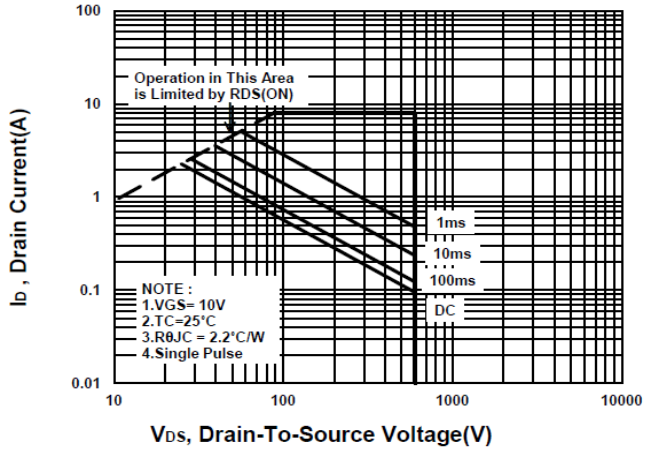
On-Resistance VS Temperature



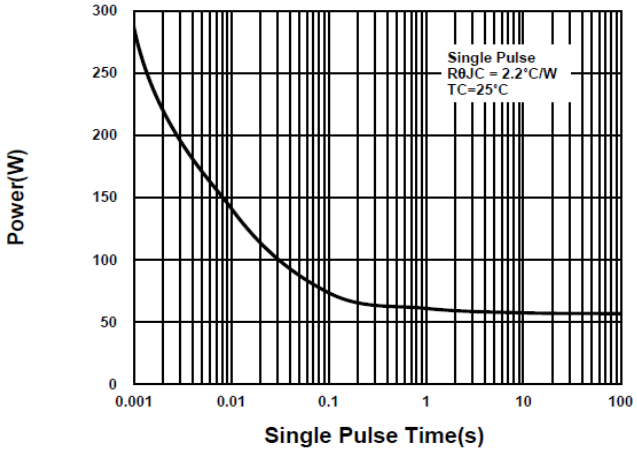
Source-Drain Diode Forward Voltage



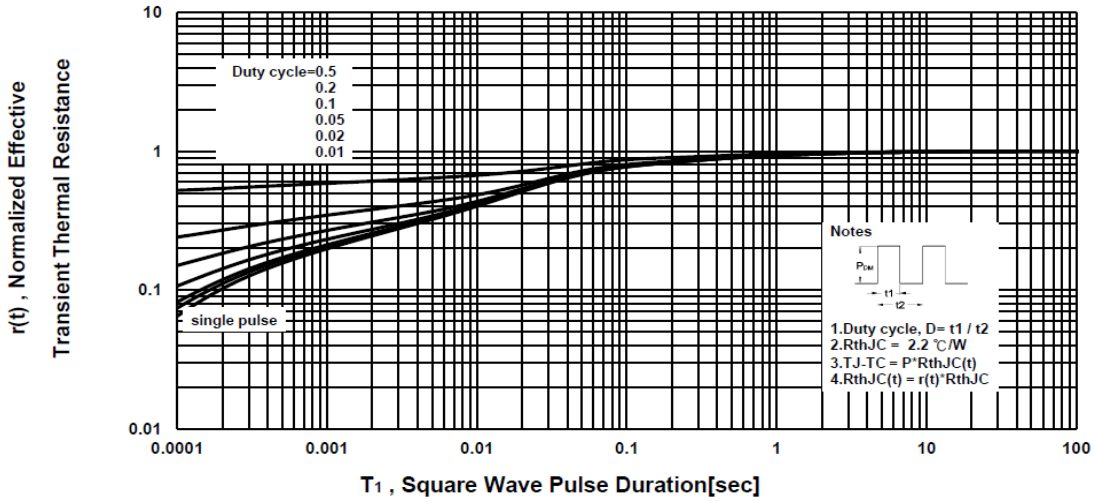
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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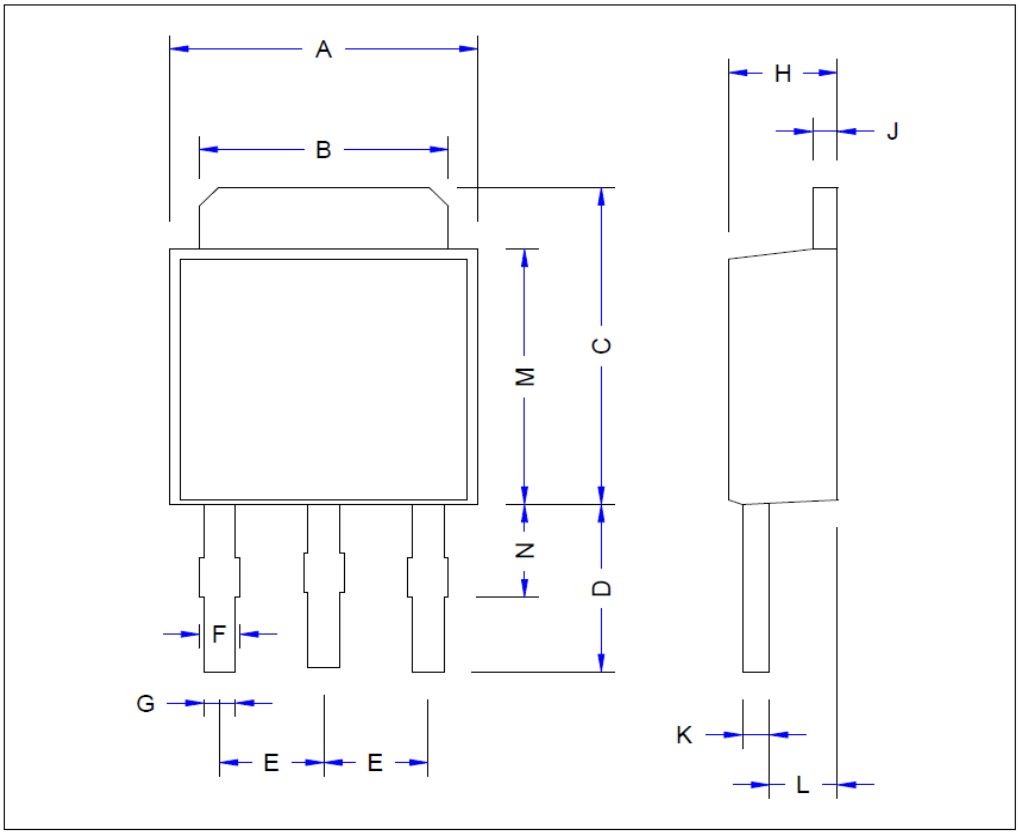
Package Dimension

TO-251 (IS) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	6.3	6.6	6.8	H	2.1	2.3	2.5
B	4.8	5.3	5.5	J	0.4	0.5	0.6
C	6.7		7.57	K	0.35	0.5	0.65
D	3	3.5	4.5	L	0.9		1.5
E		2.3		M	5.3		6.22
F	0.6	0.9	1.1	N	1.4	1.6	2.1
G	0.4		0.89				



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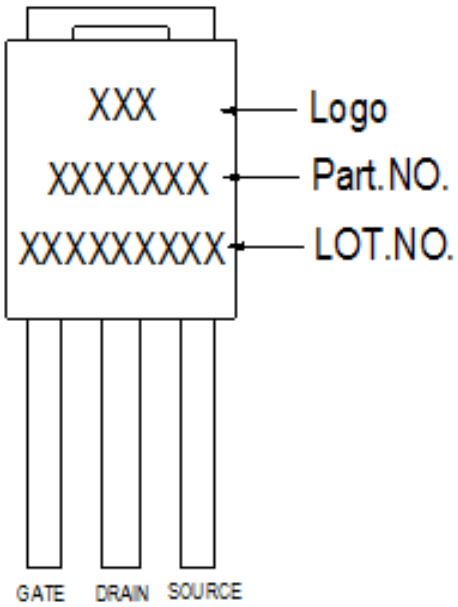
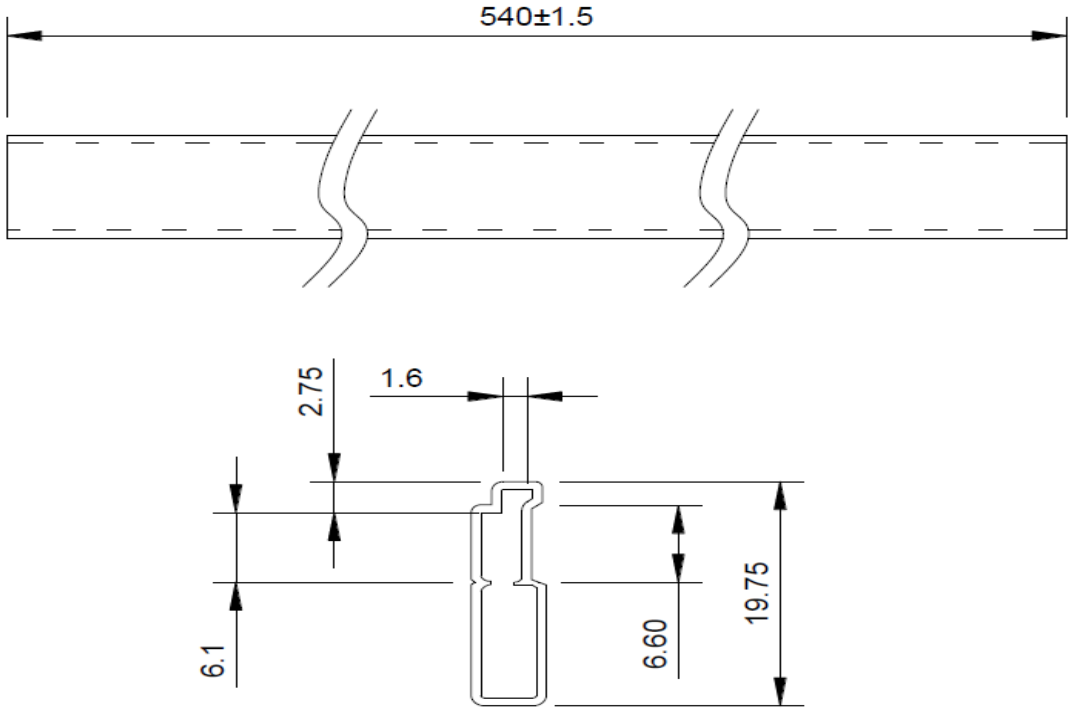
A. Marking Information



B. Tape&Reel Information:75pcs/Tube



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C. Lot.No. & Date Code rule

1.LOT.NO.

M N 15M21 03

- 03 → #8~9 Sub-lot No
- 15M21 → Order series no.
- N → Foundry site
- M → Assembly site

2.Date Code

D Y M X XXX

- XXX → Order series no. & Sub-lot No
- X → Week
- M → M : Month (A:Jan , B:Feb , C:Mar ,D :Apr ,E:May ,F:Jun,G:Jul,H:Aug,I:Sep,J:Oct,K:Nov,L:Dec.)
- Y → Y : Year (N : 2011, O : 2012 ...)
- D → Assembly site

3.Date Code (for Small package)

XX Y WW

- WW → Week
- Y → Y : Year (9: 2009,A : 2010, B : 2011 ...)
- XX → Device Name

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D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文”0”和数字”0”，”G和”Q”的字型即可)
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least